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(54) **Title:** WAFER-LEVEL MAUFACTURE OF DEVICES, IN PARTICULAR OF OPTICAL DEVICES

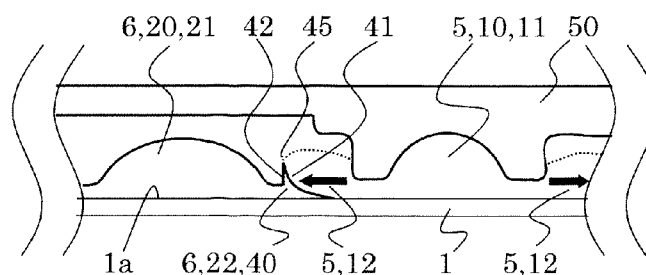


Fig. 8

(57) **Abstract:** The wafer-level method for applying $N \geq 2$ first elements (10) to a first side of a substrate (1), wherein the substrate (1) has at the first side a first surface (1a) comprises a) providing the substrate (1), wherein at least N barrier members (40) are present at the first side, and wherein each of the N barrier members (40) is associated with one of the N first elements (10). And for each of the N first elements, the method comprises b) bringing a respective first amount of a hardenable material (5) in a flowable state in contact with the first surface (1a), the respective first amount of hardenable material (5) being associated with the respective first element (10); c) controlling a flow of the respective associated first amount of hardenable material (5) on the first surface (1a) by means of the respective associated barrier member (40); d) hardening the respective associated first amount of hardenable material (5). And for each of the N first elements (10), in step d), an interconnection between the first surface (1a) and the respective element (10) is created.